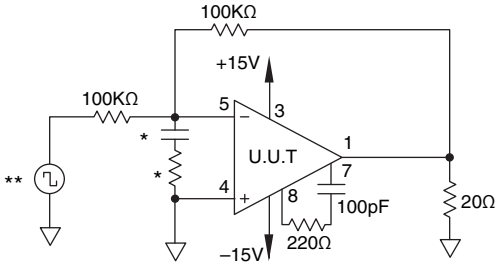
SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent Current	I_Q	25°C	±35V	V_{IN} = 0, A_V = 100		85	mA
1	Input Offset Voltage	V_{OS}	25°C	±35V	V_{IN} = 0, A_V = 100		3	mV
1	Input Offset Voltage	V_{OS}	25°C	±12V	V_{IN} = 0, A_V = 100		5.3	mV
1	Input Offset Voltage	V_{OS}	25°C	±40V	V_{IN} = 0, A_V = 100		3.5	mV
1	Input Bias Current, +IN	$+I_B$	25°C	±35V	V_{IN} = 0		100	pA
1	Inout Bias Current, –IN	$-I_B$	25°C	±35V	V_{IN} = 0		100	pA
1	Input Offset Current	I_{OS}	25°C	±35V	V_{IN} = 0		50	pA
3	Quiescent Current	I_Q	–55°C	±35V	V_{IN} = 0, A_V = 100		165	mA
3	Input Offset Voltage	V_{OS}	–55°C	±35V	V_{IN} = 0, A_V = 100		5.4	mV
3	Input Offset Voltage	V_{OS}	–55°C	±12V	V_{IN} = 0, A_V = 100		7.7	mV
3	Input Offset Voltage	V_{OS}	–55°C	±40V	V_{IN} = 0, A_V = 100		5.9	mV
3	Input Bias Current, +IN	$+I_B$	–55°C	±35V	V_{IN} = 0		100	pA
3	Input BiasCurrent, –IN	$-I_B$	–55°C	±35V	V_{IN} = 0		100	pA
3	Input Offset Current	I_{OS}	–55°C	±35V	V_{IN} = 0		50	pA
2	Quiescent Current	I_Q	125°C	±35V	V_{IN} = 0, A_V = 100		140	mA
2	Input Offset Voltage	V_{OS}	125°C	±35V	V_{IN} = 0, A_V = 100		6	mV
2	Input Offset Voltage	V_{OS}	125°C	±12V	V_{IN} = 0, A_V = 100		8.3	mV
2	Input Offset Voltage	V_{OS}	125°C	±40V	V_{IN} = 0, A_V = 100		6.5	mV
2	Input Bias Current, +IN	$+I_B$	125°C	±35V	V_{IN} = 0		10	nA
2	Input Bias Current, –IN	$-I_B$	125°C	±35V	V_{IN} = 0		10	nA
2	Input Offset Current	I_{OS}	125°C	±35V	V_{IN} = 0		10	nA
4	Output Voltage, I_O = 3A	V_O	25°C	±21.3V	R_L = 3.75Ω	11.3		V
4	Output Voltage, I_O = 66mA	V_O	25°C	±40V	R_L = 500Ω	33		V
4	Output Voltage, I_O = 2A	V_O	25°C	± 38V	R_L = 15Ω	30		V
4	Current Limits	I_{CL}	25°C	±32.2V	R_L = 3.75Ω	3.4	6	A
4	Stability/Noise	E_N	25°C	±35V	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1	mV
4	Slew Rate	SR	25°C	±35V	R_L = 500Ω	25	500	V/µs
4	Open Loop Gain	A_{OL}	25°C	±35V	R_L = 500Ω, F = 10Hz	80		dB
4	Common Mode Rejection	CMR	25°C	±34.5V	R_L = 500Ω, F = DC, V_{CM} = ±22.5V	64		dB
6	Output Voltage, I_O = 3A	V_O	–55°C	±21.3V	R_L = 3.75Ω	11.3		V
6	Output Voltage, I_O = 66mA	V_O	–55°C	±40V	R_L = 500Ω	33		V
6	Output Voltage, I_O = 2A	V_O	–55°C	±38V	R_L = 15Ω	30		V
6	Stability/Noise	E_N	–55°C	±35V	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1	mV
6	Slew Rate	SR	–55°C	±35V	R_L = 500Ω	25	500	V/µs
6	Open Loop Gain	A_{OL}	–55°C	±35V	R_L = 500Ω, F = 10Hz	80		dB
6	Common Mode Rejection	CMR	–55°C	±34.5V	R_L = 500Ω, F = DC, V_{CM} = ±22.5V	64		dB
5	Output Voltage, I_O = 66mA	V_O	125°C	±40V	R_L = 500Ω	33		V
5	Output Voltage, I_O = 1A	V_O	125°C	±23.5V	R_L = 15Ω	15		V
5	Stability/Noise	E_N	125°C	±35V	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1	mV
5	Slew Rate	SR	125°C	±35V	R_L = 500Ω,	20	500	V/µs
5	Open Loop Gain	A_{OL}	125°C	±35V	R_L = 500Ω, F = 10Hz	80		dB
5	Common Mode Rejection	CMR	125°C	±34.5V	R_L = 500Ω, F = DC, V_{CM} = ±22.5V	64		dB

BURN IN CIRCUIT



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.